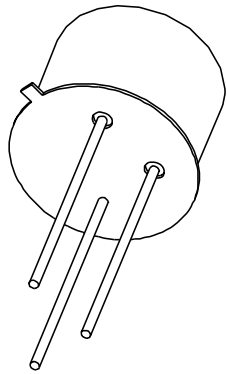


# DATA SHEET



**2N1613**

**NPN medium power transistor**

Product specification  
Supersedes data of September 1994  
File under Discrete Semiconductors, SC04

1997 Apr 11

## NPN medium power transistor

2N1613

## FEATURES

- Low current (max. 500 mA)
- Low voltage (max. 50 V).

## APPLICATIONS

- High-speed switching and amplification.

## DESCRIPTION

NPN medium power transistor in a TO-39 metal package.

## PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case

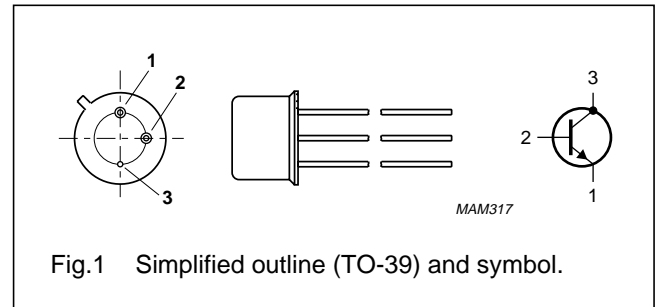


Fig.1 Simplified outline (TO-39) and symbol.

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	75	V
$V_{CEO}$	collector-emitter voltage	open base	–	50	V
$I_{CM}$	peak collector current		–	1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	0.8	W
$h_{FE}$	DC current gain	$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}$	40	120	
$f_T$	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	60	–	MHz

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	75	V
$V_{CEO}$	collector-emitter voltage	open base	–	50	V
$V_{EBO}$	emitter-base voltage	open collector	–	7	V
$I_C$	collector current (DC)		–	500	mA
$I_{CM}$	peak collector current		–	1	A
$I_{BM}$	peak base current		–	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	0.8	W
		$T_{case} = 100\text{ °C}$	–	1.7	W
		$T_{case} \leq 25\text{ °C}$	–	3	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	200	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	218	K/W
$R_{th\ j-c}$	thermal resistance from junction to case		58.3	K/W

**Note**

1. Refer to TO-39 standard mounting conditions.

## NPN medium power transistor

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**CHARACTERISTICS** $T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 150\text{ °C}$	–	10	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	10	nA
$h_{FE}$	DC current gain	$I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$	20	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	35	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ °C}$	20	–	
		$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	40	120	
		$I_C = 500\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	20	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	1.5	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	1.3	V
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}$	–	25	pF
$C_e$	emitter capacitance	$I_C = i_c = 0; V_{EB} = 0.5\text{ V}$	–	80	pF
$f_T$	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	60	–	MHz

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

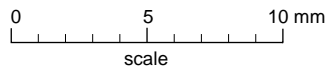
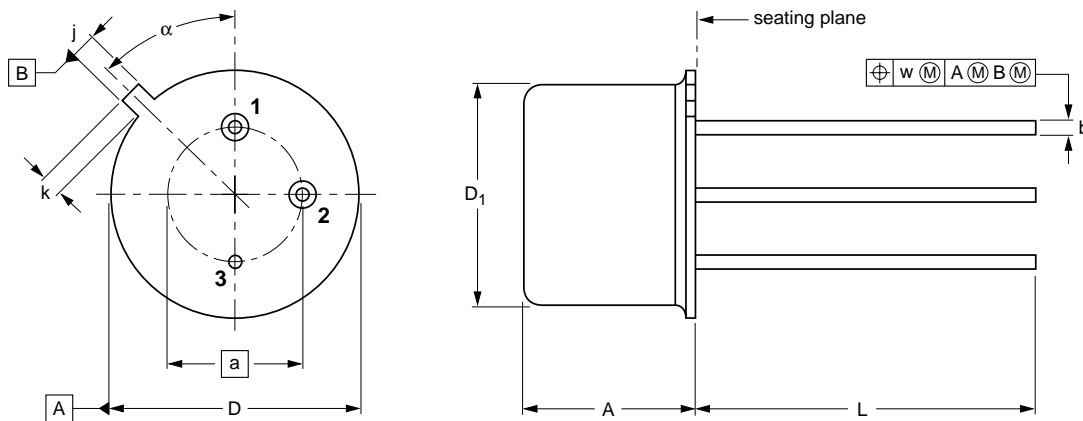
NPN medium power transistor

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PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D <sub>1</sub>	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

## NPN medium power transistor

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**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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NPN medium power transistor

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